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(54) LEVEL SHIFT CIRCUIT, CHIP AND DISPLAY DEVICE

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(57)**ABSTRACT**

Embodiments of the disclosure provide a level shift circuit, a chip and a display device. By setting first and second voltage clamping modules, and by adjusting first clamping voltage by controlling bias voltage input to the first voltage clamping module and adjusting second clamping voltage by controlling bias voltage and second bias voltage input to the second voltage clamping module, respective operating and output voltages of the first and the second voltage clamping modules and the shift module are within small range. Therefore, even the level shift circuit is designed by using devices with breakdown voltage lower than the difference between the first and second power supply voltages, the devices in the level shift circuit may be avoid being breakdown. Accordingly, some process platforms that cannot produce high-breakdown voltage devices may produce chips including the level shift circuit in the embodiment, and the restrictions on the process platform are reduced.

